

FGPF4565 650 V Field Stop Trench IGBT

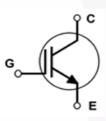
Features

- High Current Capability
- Low Saturation Voltage: V_{CE(sat)} =1.5 V(Typ.) @ I_C = 30 A
- High Input Impedance
- RoHS Compliant

Applications

• IPL (Intense Pulsed Light)

G C E TO-220F (Retractable)



Using innovative field stop IGBT technology, Fairchild's new series of field stop trench IGBTs offer the optimum performance

General Description

for IPL (Intense Pulsed Light).

Absolute Maximum Ratings TC = 25°C unless otherwise noted

Symbol	Description		Ratings	Unit	
V _{CES}	Collector to Emitter Voltage		650	V	
V _{GES}	Gate to Emitter Voltage		± 25	V	
I _{C pulse (1)*}	Pulsed Collector Current	@ T _C = 25°C	170	A	
P _D	Maximum Power Dissipation	@ T _C = 25 ^o C	30	W	
	Maximum Power Dissipation	@ T _C = 100 ^o C	12	W	
TJ	Operating Junction Temperature		-55 to +150	°C	
T _{stg}	Storage Temperature Range		-55 to +150	°C	
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	°C		

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	-	4.1	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	-	62.5	°C/W

Notes:

1. Half sine wave: D< 0.01, pulse width < 1usec,

* Ic pulse limit by max Tj

November 2014

Part Nu	nber	Top Mark	Package	Packing Method	Reel Size	Tape Wi	dth Q	uantity
FGPF4565 FGPF4565 TO-220F		Tube	N/A	N/A		50		
Electric	al Cha	aracteristics	s of the IC	BT T _C = 25°C unless otherv	<i>v</i> ise noted			
Symbol		Paramete		Test Condition		. Тур.	Max.	Unit
Off Charac	teristics							
BV _{CES}	Collecto	or to Emitter Break	lown Voltage	V _{GE} = 0 V, I _C = 1 mA	650	-	-	V
ΔBV _{CES} / ΔT _J	Temperature Coefficient of Breakdown Voltage		$V_{GE} = 0 V, I_C = 1 mA$		0.65	-	V/ºC	
ICES	Collecto	Collector Cut-Off Current		V _{CE} = V _{CES} , V _{GE} = 0 V -		-	250	μA
I _{GES}	G-E Leakage Current			$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	±400	nA
On Charac	eristics							
V _{GE(th)}	G-E Th	reshold Voltage		I _C = 250 μA, V _{CE} = V _{GE}	3.0	4.0	5.0	V
				$I_{\rm C} = 20$ A, $V_{\rm GE} = 15$ V	-	1.35	-	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage		I _C = 30 A, V _{GE} = 15 V	-	1.50	1.88	V	
				$I_{C} = 30 \text{ A}, V_{GE} = 15 \text{ V},$ $T_{C} = 150^{\circ}\text{C}$	-	1.75	-	v
Dynamic C	haracter	istics						
C _{ies}	-	apacitance			-	1650	-	pF
C _{oes}	-	Capacitance		$V_{CE} = 30 V, V_{GE} = 0 V,$	-	34	-	pF
C _{res}	Reverse Transfer Capacitance		f = 1 MHz	-	17	-	pF	
Switching	Characte	eristics						
t _{d(on)}	Turn-Or	n Delay Time			-	11.2	-	ns
t _r	Rise Tir	ne		$V_{CC} = 400 \text{ V}, I_{C} = 30 \text{ A},$	-	44.8	-	ns
t _{d(off)}	Turn-Of	f Delay Time		$R_G = 5 \Omega$, $V_{GE} = 15 V$, Resistive Load, $T_C = 25^{\circ}$	c -	40.8	- /	ns
t _f	Fall Tim	e			-	153	-	ns
t _{d(on)}	Turn-Or	n Delay Time			-	12.8	-	ns
t _r	Rise Tir	ne		$V_{CC} = 400 \text{ V}, \text{ I}_{C} = 30 \text{ A},$	-	59.2	-	ns
t _{d(off)}	Turn-Of	f Delay Time		$R_G = 5 \Omega$, $V_{GE} = 15 V$, Resistive Load, $T_C = 150$	°C -	40.8	-	ns
t _f	Fall Tim	ie			-	202	-	ns
Qg	Total Ga	ate Charge			-	40.3	-	nC
Q _{ge}	Gate to	Emitter Charge		$V_{CE} = 400 \text{ V}, I_{C} = 30 \text{ A},$ $V_{GE} = 15 \text{ V}$	-	8.8	-	nC
Q _{gc}	Gate to	Collector Charge		GE - 10 V	-	10.4	<u> </u>	nC

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Typical Performance Characteristics Figure 1. Typical Output Characteristics Figure 2. Typical Output Characteristics 180 180 20V T_C = 25^oC T_C = 150[°]C 12V 10V 5\ 12V 150 150 Collector Current, I_c [A] 20\ Collector Current, Ic [A] 10V 120 120 15V 90 90 V_{GE} = 8V V_{GE} = 8V 60 60 30 30 0 0 0 2 3 4 5 0 2 3 4 5 6 6 1 Collector-Emitter Voltage, V_{CE} [V] Collector-Emitter Voltage, V_{CE} [V] Figure 4. Saturation Voltage vs. Case Figure 3. Typical Saturation Voltage **Characteristics Temperature at Variant Current Level** 2.5 180 Common Emitter $V_{GE} = 15V$ Collector-Emitter Voltage, V_{CE} [V] 150 Collector Current, Ic [A] 60A 2 120 90 30A 60 Common Emitter V_{GE} = 15V T_C = 25^oC ____ 30 T_C = 150^oC ... I_C = 15A 1 0 -55 -30 0 30 60 90 120 0 2 3 4 5 6 Collector-Emitter Case Temperature, T_C [°C] Collector-Emitter Voltage, V_{CE} [V] Figure 5. Saturation Voltage vs. V_{GE} Figure 6. Saturation Voltage vs. V_{GE} 20 20 Common Emitter Common Emitter T_C = 150^oC Collector-Emitter Voltage, V_{CE} [V] $T_c = 25^{\circ}C$ Collector-Emitter Voltage, V_{CE} [V] 16 16 12 12 $I_{\rm C} = 15A$ $I_{\rm C} = 15A$ 30A 30A 8 8 60A 60A 4 Δ 0 ∟ 4 0 8 12 16 20 4 8 12 16 Gate-Emitter Voltage, V_{GE} [V] Gate-Emitter Voltage, V_{GE} [V] ©2014 Fairchild Semiconductor Corporation

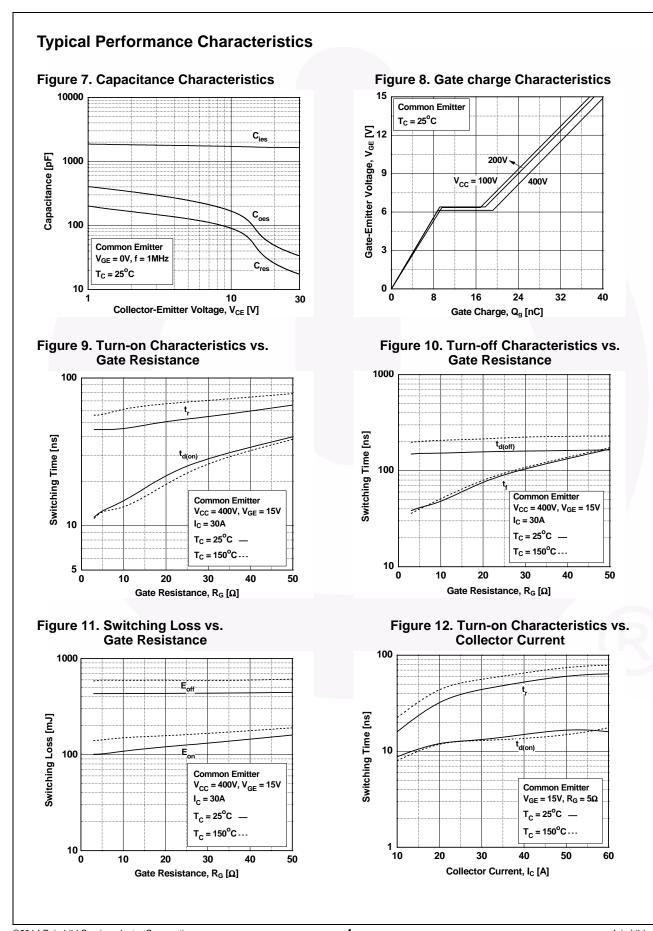
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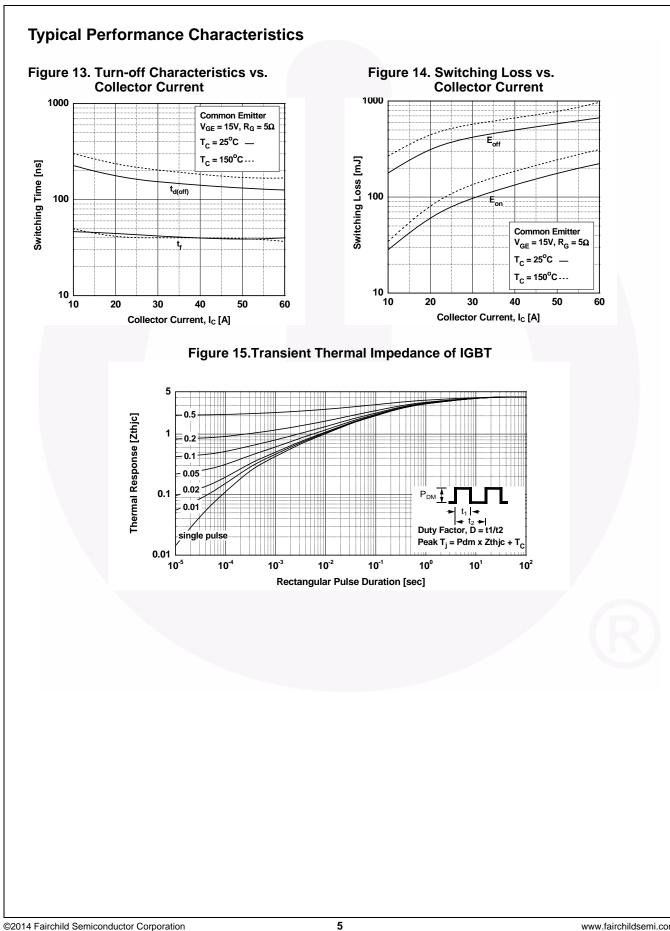
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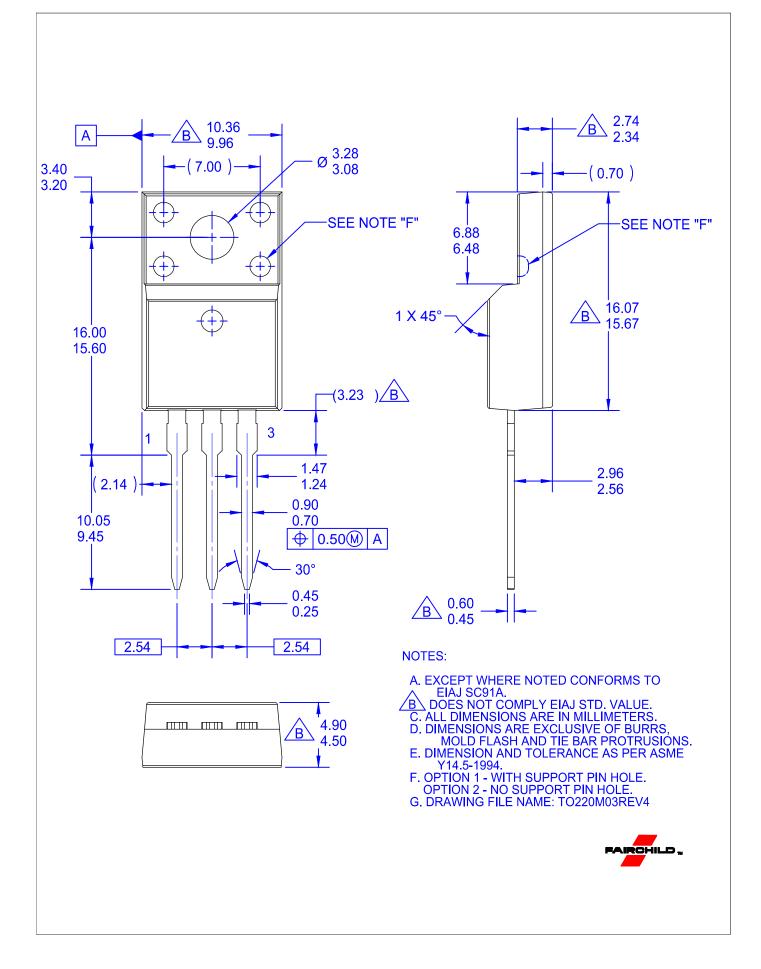


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